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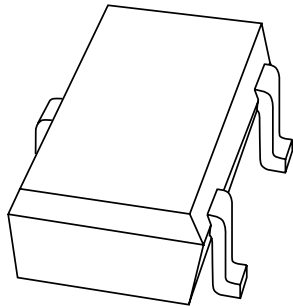
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via salesaddresses@nexperia.com). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



PMSS3904 NPN switching transistor

Product data sheet
Supersedes data of 1997 Sep 03

1999 May 27

NPN switching transistor

PMSS3904

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- General purpose switching and amplification
- Telephony and professional communication equipment.

DESCRIPTION

NPN switching transistor in an SC-70 (SOT323) plastic package. PNP complement: PMSS3906.

MARKING CODE

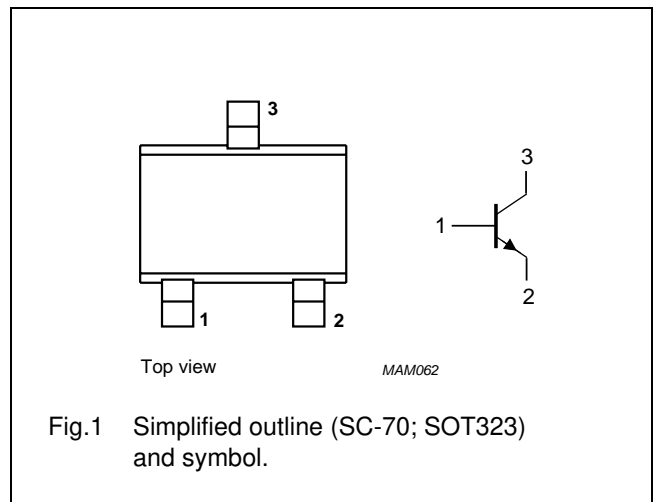
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMSS3904	*04

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	60	V
V _{CEO}	collector-emitter voltage	open base	–	40	V
V _{EBO}	emitter-base voltage	open collector	–	6	V
I _C	collector current (DC)		–	100	mA
I _{CM}	peak collector current		–	200	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

PMSS3904

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	50	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$; see Fig.2			
		$I_C = 0.1\text{ mA}$	40	–	
		$I_C = 1\text{ mA}$	70	–	
		$I_C = 10\text{ mA}$	100	300	
		$I_C = 50\text{ mA}$; note 1	60	–	
		$I_C = 100\text{ mA}$; note 1	30	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	200	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$; note 1	–	300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	650	850	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$; note 1	–	950	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	4	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	180	–	MHz
F	noise figure	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega$ $f = 10\text{ Hz to }15.7\text{ KHz}$	–	5	dB

Switching times (between 10% and 90% levels); see Fig.3

t_{on}	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 1\text{ mA};$ $I_{Boff} = -1\text{ mA}; V_{CC} = 3\text{ V};$ $V_{BB} = -1.9\text{ V}$	–	110	ns
t_d	delay time		–	50	ns
t_r	rise time		–	60	ns
t_{off}	turn-off time		–	1200	ns
t_s	storage time		–	1000	ns
t_f	fall time		–	200	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

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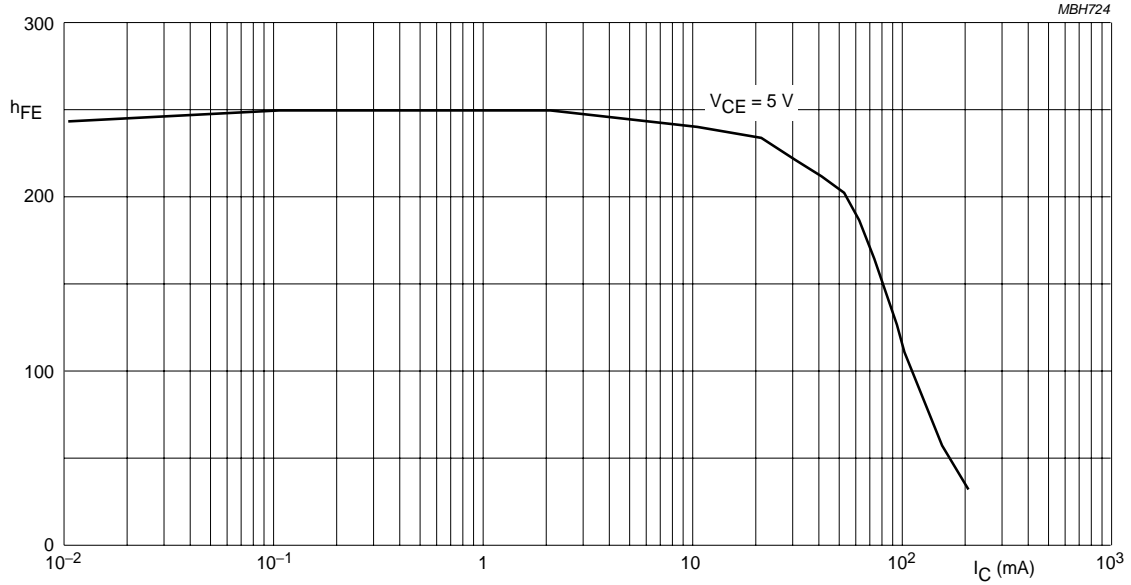
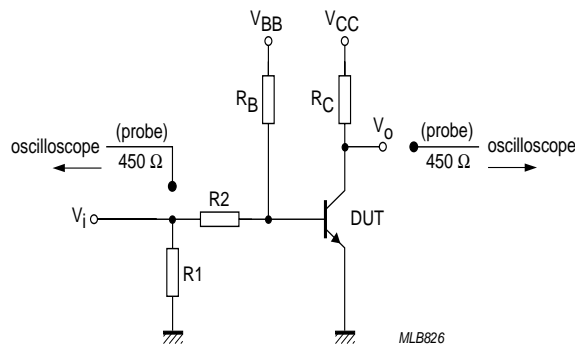


Fig.2 DC gain current; typical values.



$V_i = 5\text{ V}$; $T = 500\ \mu\text{s}$; $t_p = 10\ \mu\text{s}$; $t_r = t_f \leq 3\ \text{ns}$.
 $R_1 = 56\ \Omega$; $R_2 = 2.5\ \text{k}\Omega$; $R_B = 3.9\ \text{k}\Omega$; $R_C = 270\ \Omega$.
 Oscilloscope: input impedance $Z_i = 50\ \Omega$.

Fig.3 Test circuit for switching times.

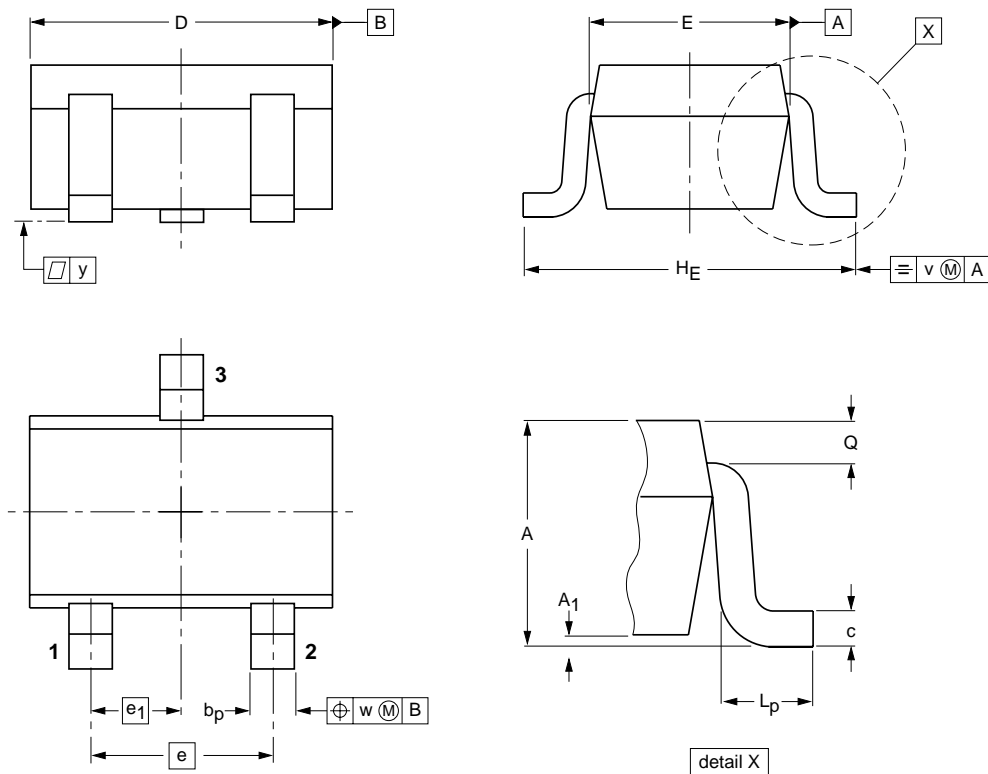
NPN switching transistor

PMSS3904

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN switching transistor

PMSS3904

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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Contact information

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